Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D T_A = +25°C
30V	0.4Ω @ V_{GS} = 10V	0.9A
	0.7Ω @ V_{GS} = 4.5V	0.7A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface-Mount Package
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC converters
- Load switches
- Power-management functions

Mechanical Data

- Package: SOT523
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)

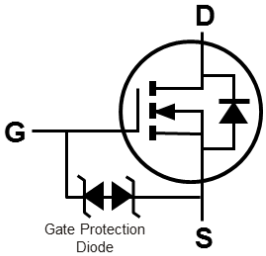


ESD PROTECTED

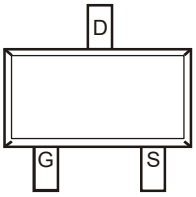
SOT523



Top View



Equivalent Circuit



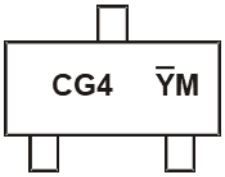
Top View

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMN3401LT-7	SOT523	3000	Tape & Reel
DMN3401LT-13	SOT523	10000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



CG4 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: M = 2025)
M = Month (ex: 9 = September)

Date Code Key

Year	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034	2035	2036
Code	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings @T_A = +25°C, unless otherwise specified.

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +75°C	I_D	0.9 0.7	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	0.45	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	5	A

Thermal Characteristics @T_A = +25°C, unless otherwise specified.

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.39	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	319	°C/W
Total Power Dissipation (Note 6)		P_D	0.49	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	254	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Electrical Characteristics @T_A = +25°C, unless otherwise specified.

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 30V, V_{GS} = 0
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±20V, V_{DS} = 0
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.8	—	1.6	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.17	0.4	Ω	V_{GS} = 10V, I_D = 0.59A
		—	0.24	0.7		V_{GS} = 4.5V, I_D = 0.2A
Diode Forward Voltage	V_{SD}	—	0.6	1.2	V	V_{GS} = 0, I_S = 10mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	50	—	pF	V_{DS} = 15V, V_{GS} = 0, f = 1.0MHz
Output Capacitance	C_{oss}	—	12	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	10	—	pF	
Total Gate Charge	Q_g	—	0.2	—	nC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 1A
Gate-Source Charge	Q_{gs}	—	0.1	—	nC	
Gate-Drain Charge	Q_{gd}	—	3.5	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.3	—	ns	V_{GS} = 10V, V_{DS} = 30V, I_D = 100mA, R_G = 25Ω
Turn-On Rise Time	t_R	—	16.8	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	13.8	—	ns	
Turn-Off Fall Time	t_F	—	50	—	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

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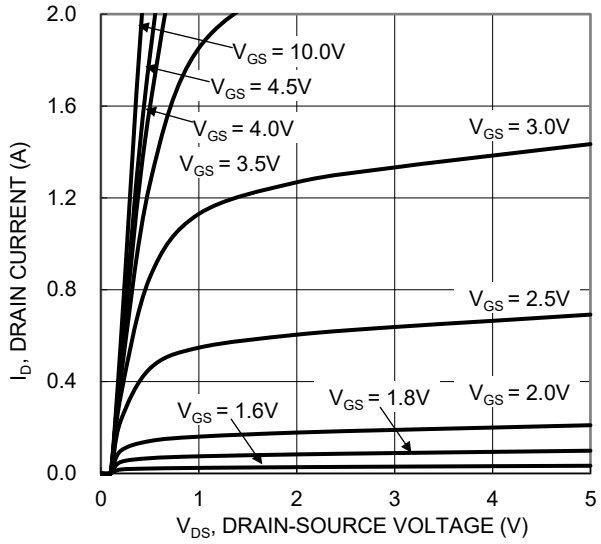


Figure 1. Typical Output Characteristic

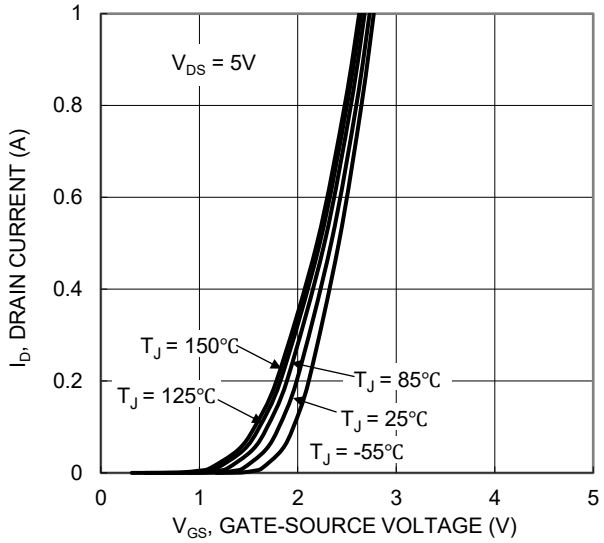


Figure 2. Typical Transfer Characteristic

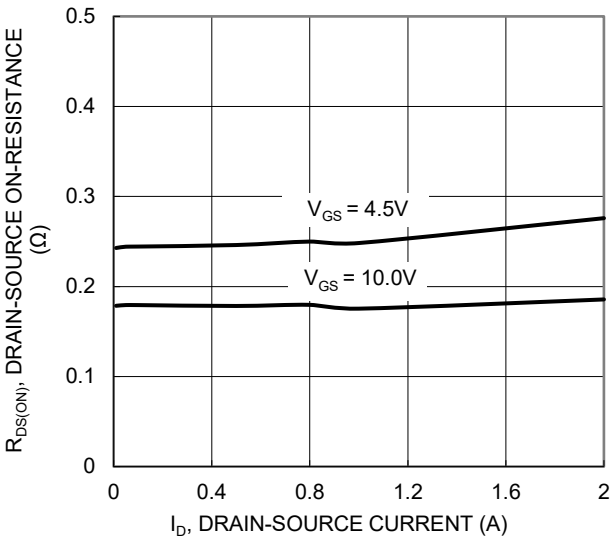


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

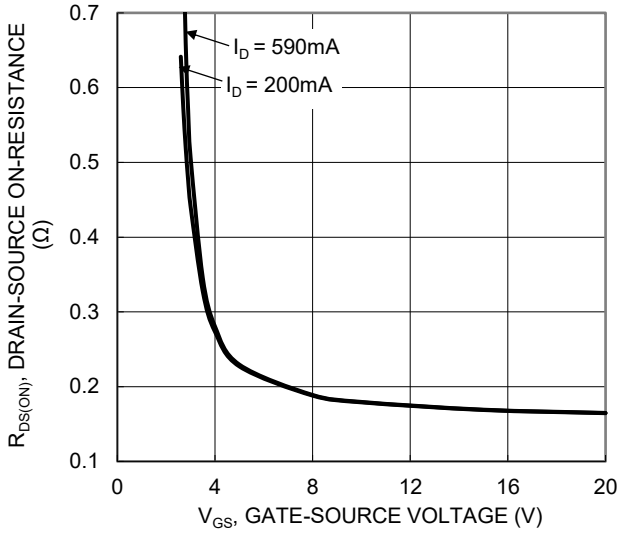


Figure 4. Typical Transfer Characteristic

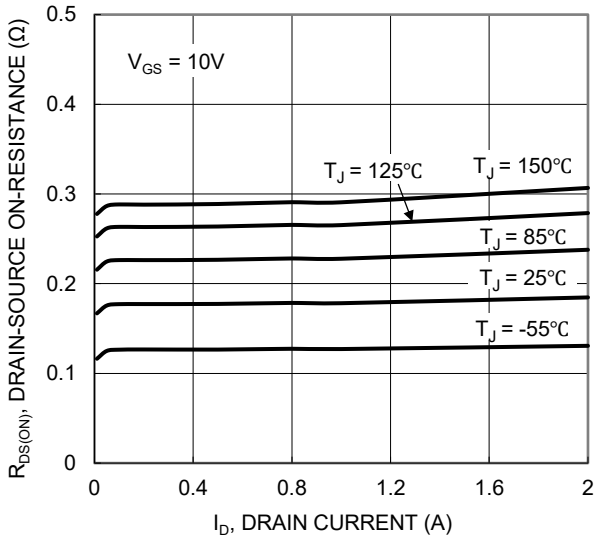


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

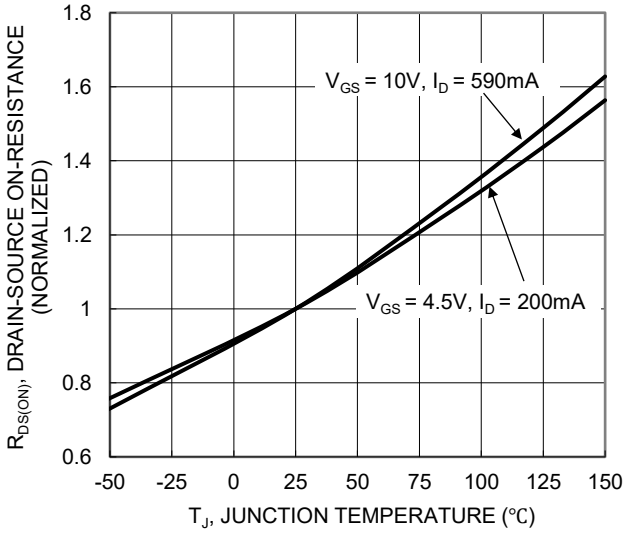


Figure 6. On-Resistance Variation with Temperature

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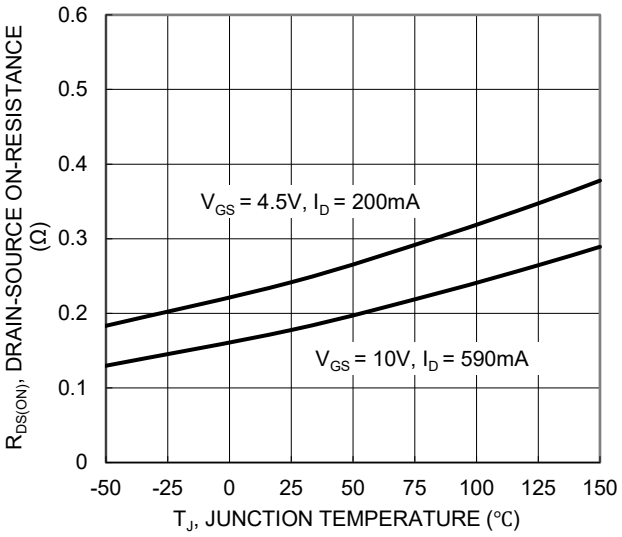


Figure 7. On-Resistance Variation with Temperature

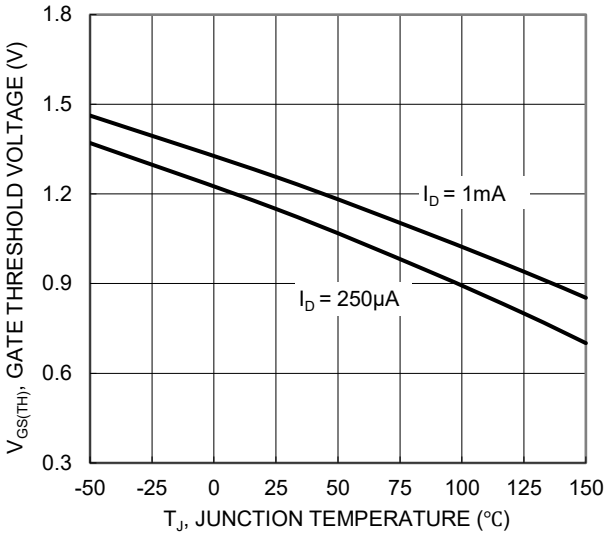


Figure 8. Gate Threshold Variation vs. Junction Temperature

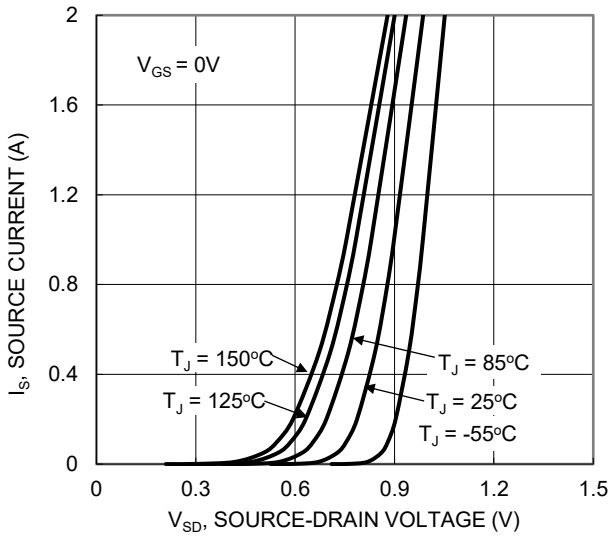


Figure 9. Diode Forward Voltage vs. Current

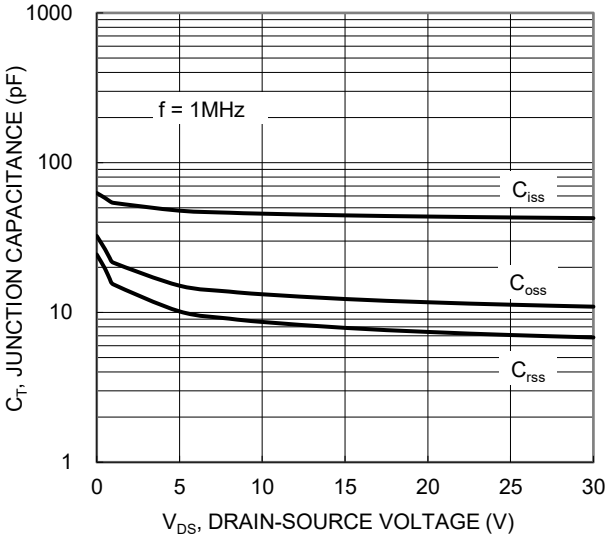


Figure 10. Typical Junction Capacitance

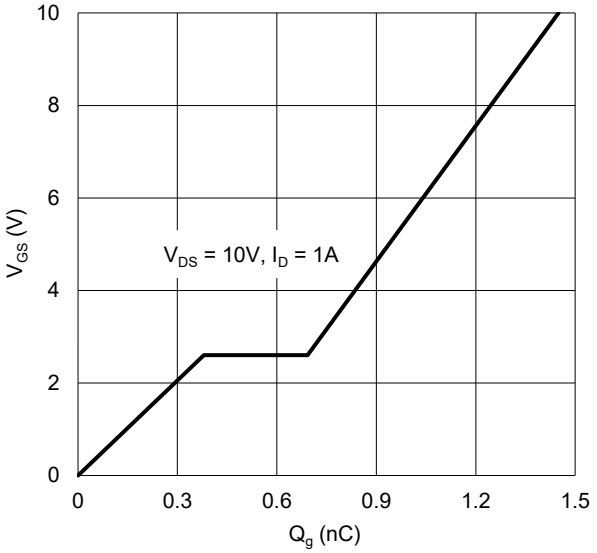


Figure 11. Gate Charge

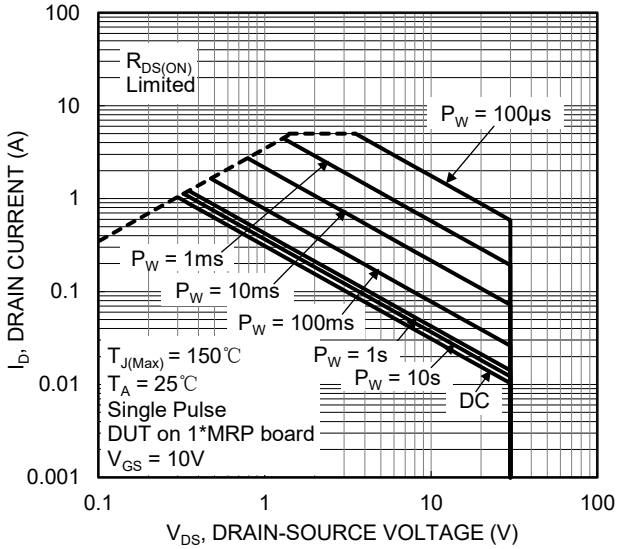


Figure 12. SOA, Safe Operation Area

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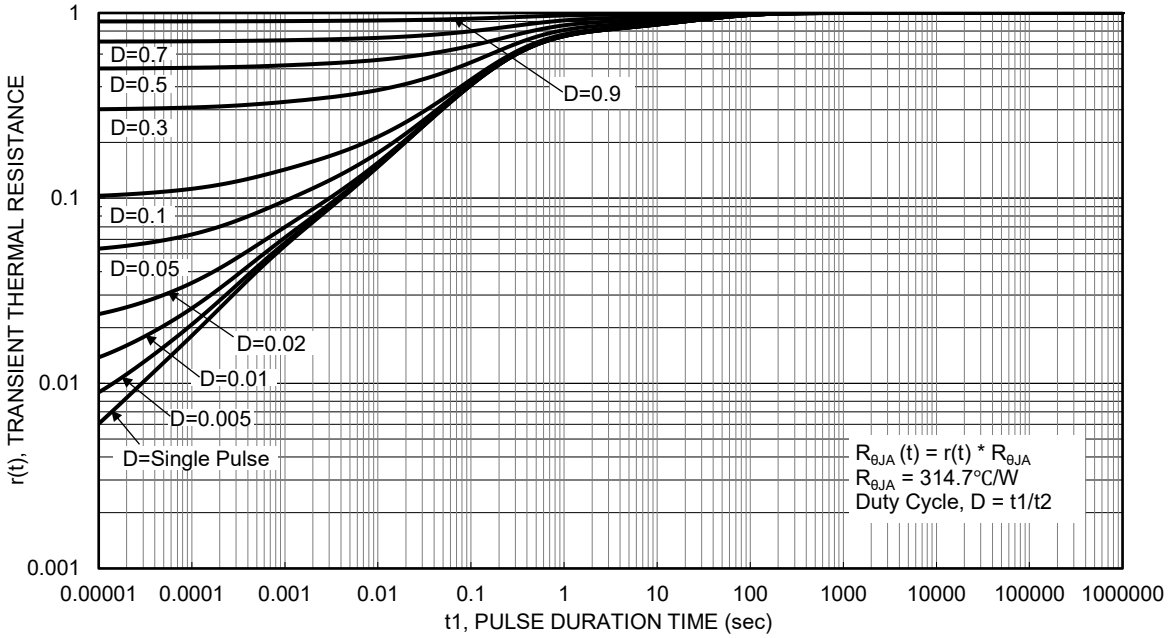


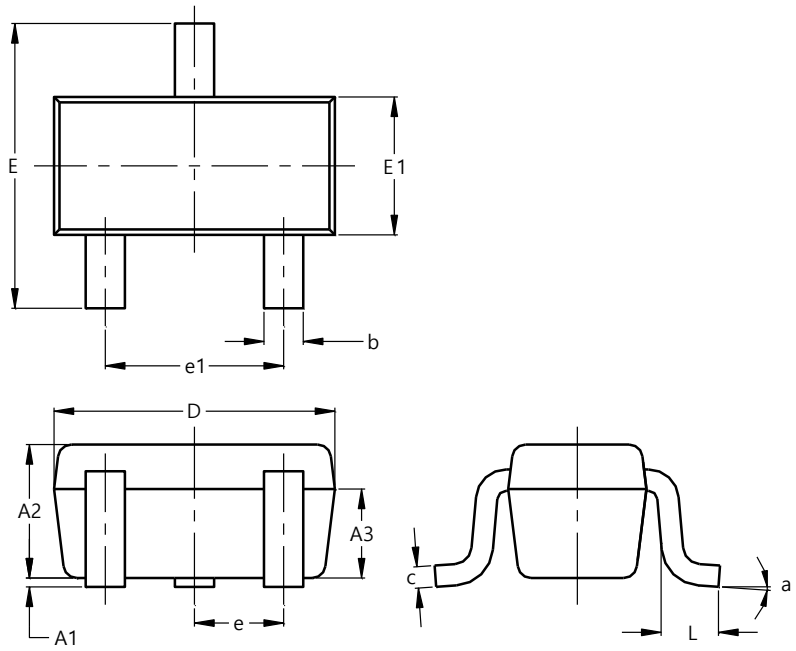
Figure 13. Transient Thermal Resistance

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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

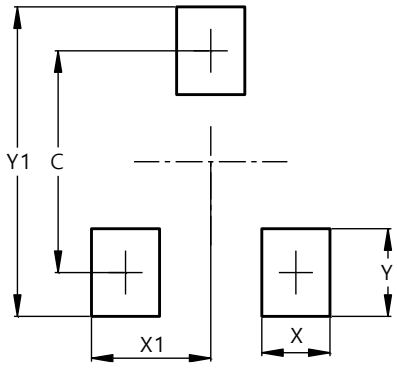


SOT523			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.60	0.80	0.75
A3	0.45	0.65	0.50
b	0.15	0.30	0.22
c	0.10	0.20	0.12
D	1.50	1.70	1.60
E	1.45	1.75	1.60
E1	0.75	0.85	0.80
e	0.50 BSC		
e1	0.90	1.10	1.00
L	0.20	0.40	0.33
a	0°	--	8°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)
C	1.29
X	0.40
X1	0.70
Y	0.51
Y1	1.80

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